

Silicon NPN Power Transistors

2SC3026

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- High voltage power switching character
- display horizontal deflection output

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

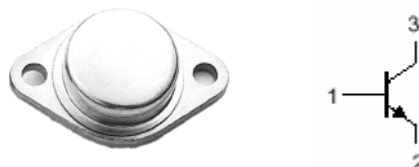


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1700	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CP}	Collector current-peak		6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-45~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA; R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA; I_C=0$	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=5A; I_B=1.25A$			2.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=5A; I_B=1.25A$			1.5	V
I_{CES}	Collector cut-off current	$V_{CE}=1700V; R_{BE}=\infty$			0.5	mA

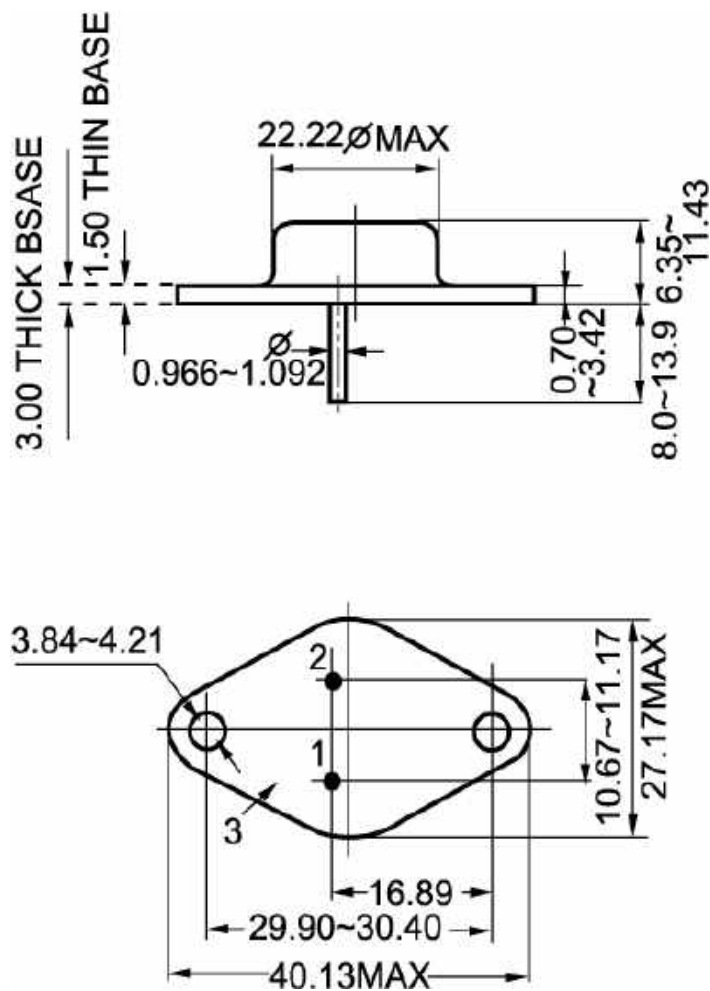
Switching times

t_s	Storage time	$I_C=5A; I_{B1}=1A; I_{B2}=-2.5A$		4.0		μs
t_f	Fall time				0.5	μs

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)